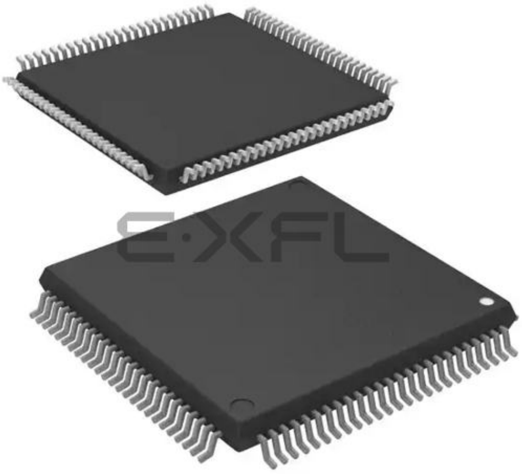
Renesas Electronics America Inc - R5F100PGDFB#50 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pgdfb-50

Table 1-1. List of Ordering Part Numbers

(2/12)

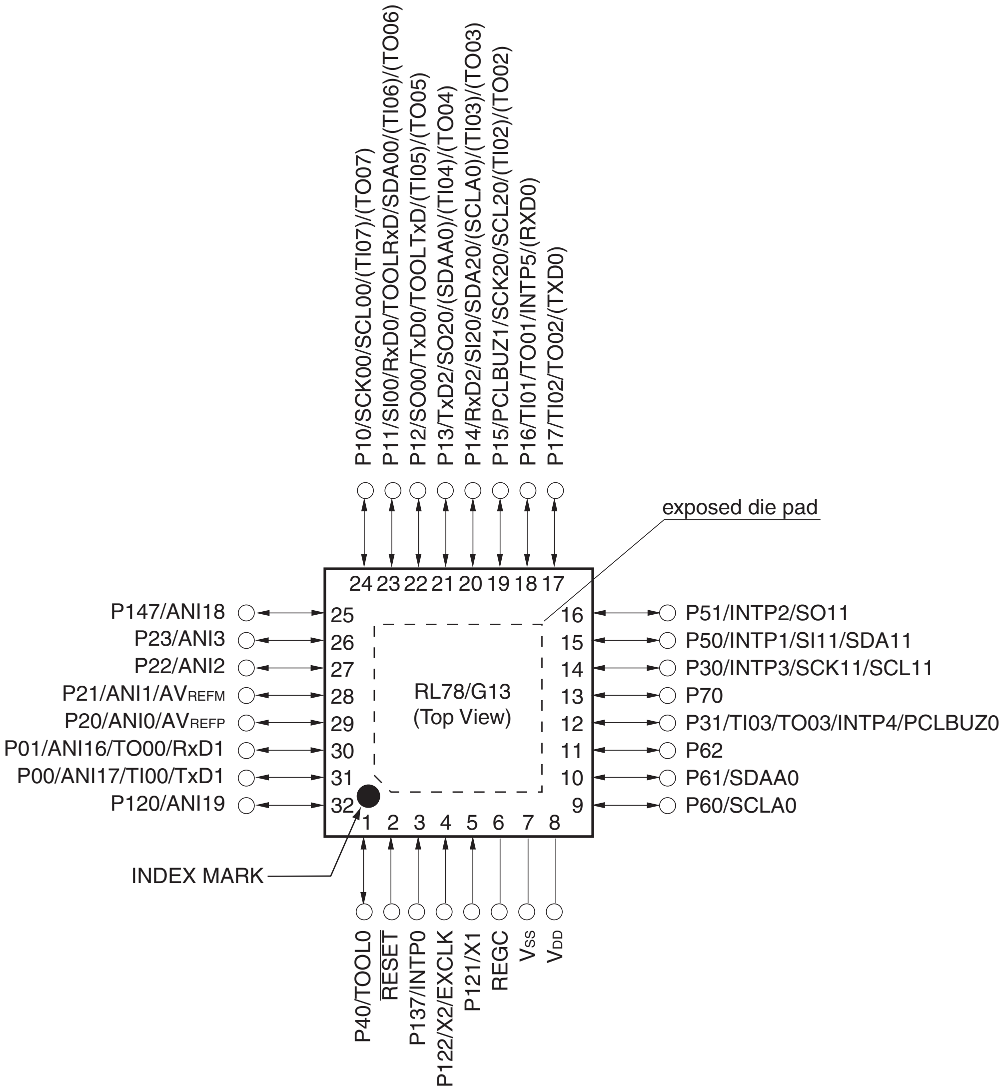
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
25 pins	25-pin plastic WFLGA (3 × 3 mm, 0.5 mm pitch)	Mounted	A	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0, R5F1008EALA#U0 R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0, R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0, R5F1008EGLA#U0 R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0, R5F1008EGLA#W0
		Not mounted	A	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0, R5F1018EALA#U0 R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0, R5F1018EALA#W0
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0, R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0 R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0 R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0, R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0 R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AAGSP#V0, R5F100ACGSP#V0, R5F100ADGSP#V0,R5F100AEGSP#V0, R5F100AFGSP#V0, R5F100AGGSP#V0 R5F100AAGSP#X0, R5F100ACGSP#X0, R5F100ADGSP#X0,R5F100AEGSP#X0, R5F100AFGSP#X0, R5F100AGGSP#X0
		Not mounted	A	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0, R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0 R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0, R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0, R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0 R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0, R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)	Mounted	A	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0, R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0 R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0, R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0, R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0 R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0, R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0, R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0 R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0, R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not mounted	A	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0, R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0 R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0, R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			D	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BFDNA#U0, R5F101BGDNA#U0 R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0, R5F101BEDNA#W0, R5F101BFDNA#W0, R5F101BGDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.5 32-pin products

- 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

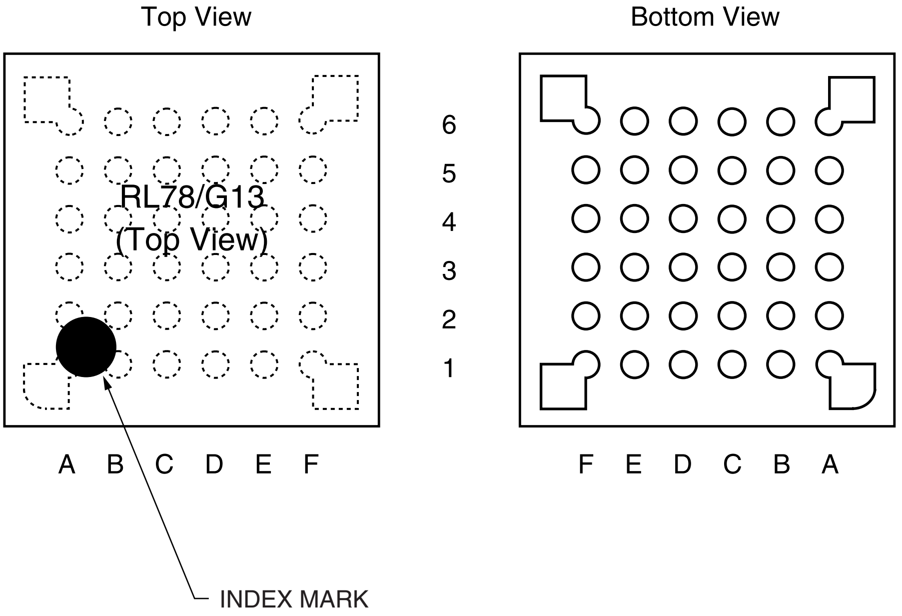
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

3. It is recommended to connect an exposed die pad to V_{SS}.

1.3.6 36-pin products

- 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	A	B	C	D	E	F	
6	P60/SCLA0	V_{DD}	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62	P61/SDAA0	V_{SS}	REGC	$\overline{\text{RESET}}$	P120/ANI19	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AV_{REFP}	P21/ANI1/ AV_{REFM}	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	A	B	C	D	E	F	

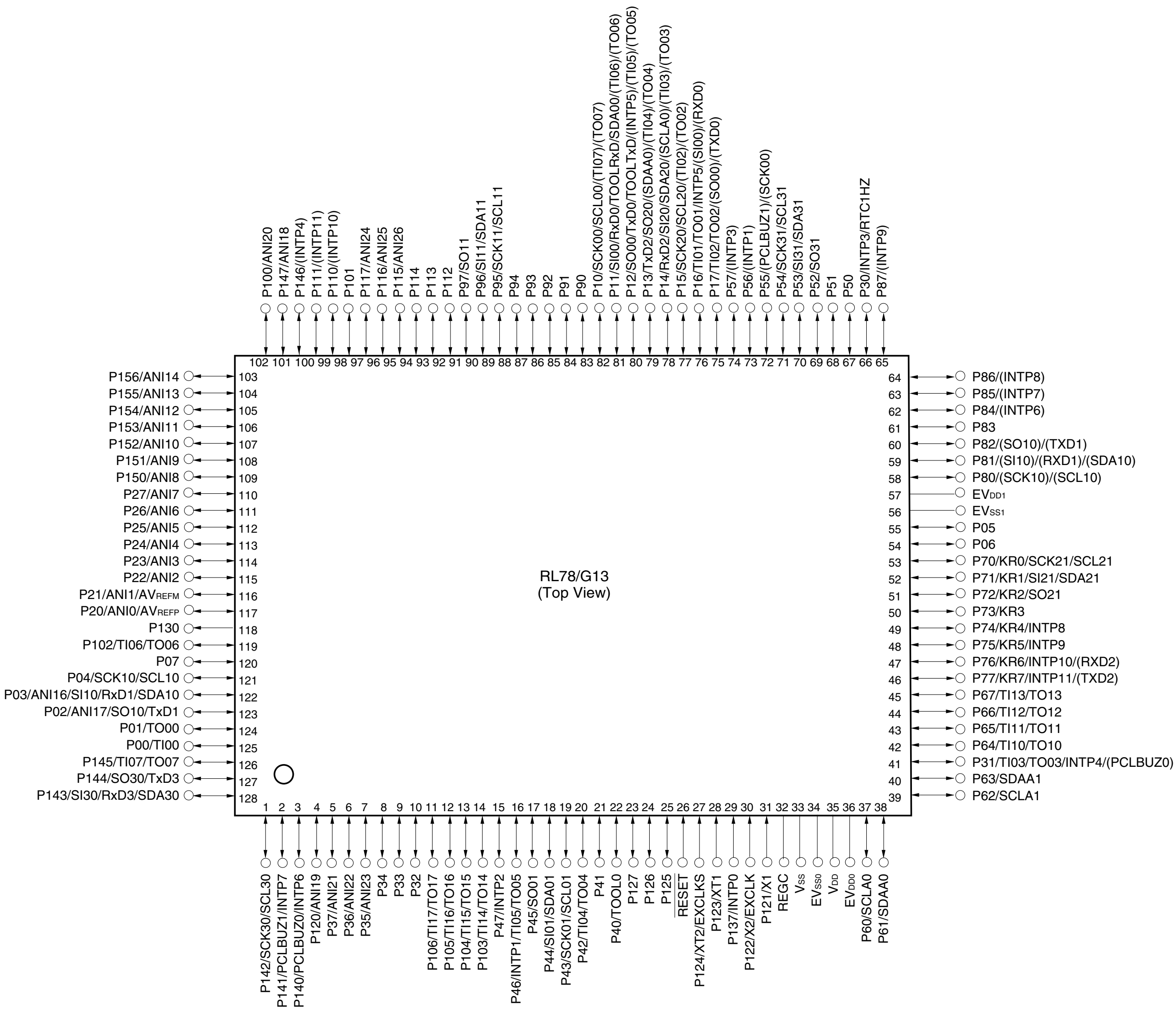
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.14 128-pin products

- 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



Cautions 1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).

3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

Notes **1.** Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
	2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode:	1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD2} [Note 2]	HALT mode	HS (high-speed main) mode [Note 7]	f_{IH} = 32 MHz [Note 4]	V_{DD} = 5.0 V		0.62	1.86	mA
					V_{DD} = 3.0 V		0.62	1.86	mA
				f_{IH} = 24 MHz [Note 4]	V_{DD} = 5.0 V		0.50	1.45	mA
					V_{DD} = 3.0 V		0.50	1.45	mA
				f_{IH} = 16 MHz [Note 4]	V_{DD} = 5.0 V		0.44	1.11	mA
					V_{DD} = 3.0 V		0.44	1.11	mA
			LS (low-speed main) mode [Note 7]	f_{IH} = 8 MHz [Note 4]	V_{DD} = 3.0 V		290	620	μA
					V_{DD} = 2.0 V		290	620	μA
			LV (low-voltage main) mode [Note 7]	f_{IH} = 4 MHz [Note 4]	V_{DD} = 3.0 V		440	680	μA
					V_{DD} = 2.0 V		440	680	μA
			HS (high-speed main) mode [Note 7]	f_{MX} = 20 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 20 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
			LS (low-speed main) mode [Note 7]	f_{MX} = 8 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
				f_{MX} = 8 MHz [Note 3], V_{DD} = 2.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
			Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 5] T_A = −40°C	Square wave input		0.28	0.61	μA
					Resonator connection		0.47	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +25°C	Square wave input		0.34	0.61	μA
					Resonator connection		0.53	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +50°C	Square wave input		0.41	2.30	μA
					Resonator connection		0.60	2.49	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +70°C	Square wave input		0.64	4.03	μA
					Resonator connection		0.83	4.22	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +85°C	Square wave input		1.09	8.04	μA
					Resonator connection		1.28	8.23	μA
	I_{DD3} [Note 6]	STOP mode [Note 8]	T_A = −40°C				0.19	0.52	μA
			T_A = +25°C				0.25	0.52	μA
			T_A = +50°C				0.32	2.21	μA
			T_A = +70°C				0.55	3.94	μA
			T_A = +85°C				1.00	7.95	μA

(**Notes** and **Remarks** are listed on the next page.)

(5) During communication at same potential (simplified I^2C mode) (1/2)

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		1850		1850		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV_{DD0} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV_{DD0} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		1850		1850		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

($T_A = -40$ to $+85°C$, $1.8\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$			$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 4		5.3		1.3		0.6	Mbps
			$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$			$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 4		5.3		1.3		0.6	Mbps
			$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V$			$f_{MCK}/6$ Notes 1 to 3		$f_{MCK}/6$ Notes 1, 2		$f_{MCK}/6$ Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 4		5.3		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. Use it with $EV_{DD0} \ge V_b$.

3. The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.

$2.4\ V \le EV_{DD0} < 2.7\ V$: MAX. 2.6 Mbps
$1.8\ V \le EV_{DD0} < 2.4\ V$: MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	32 MHz ($2.7\ V \le V_{DD} \le 5.5\ V$)
	16 MHz ($2.4\ V \le V_{DD} \le 5.5\ V$)
LS (low-speed main) mode:	8 MHz ($1.8\ V \le V_{DD} \le 5.5\ V$)
LV (low-voltage main) mode:	4 MHz ($1.6\ V \le V_{DD} \le 5.5\ V$)

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

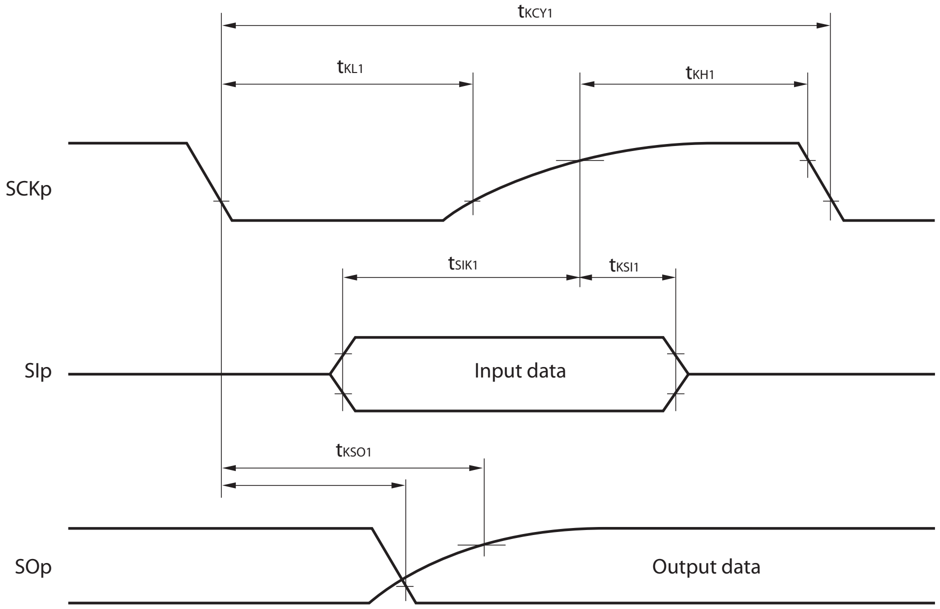
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 1	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

Notes
1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
2. Use it with EV_{DD0} ≥ V_b.

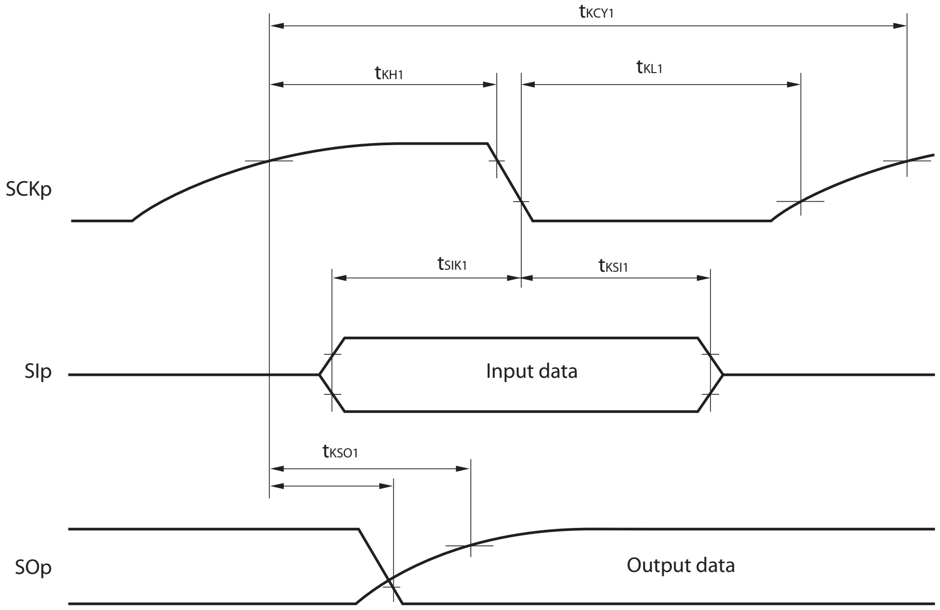
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = −40 to +85°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V_{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V_{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.54	2.90	mA
					V_{DD} = 3.0 V		0.54	2.90	mA
				f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.44	2.30	mA
					V_{DD} = 3.0 V		0.44	2.30	mA
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.40	1.70	mA
					V_{DD} = 3.0 V		0.40	1.70	mA
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	1.90	mA
					Resonator connection		0.45	2.00	mA
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	1.90	mA
					Resonator connection		0.45	2.00	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = −40°C	Square wave input		0.25	0.57	μA
					Resonator connection		0.44	0.76	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.30	0.57	μA
					Resonator connection		0.49	0.76	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.37	1.17	μA
					Resonator connection		0.56	1.36	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.53	1.97	μA
					Resonator connection		0.72	2.16	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		0.82	3.37	μA
					Resonator connection		1.01	3.56	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +105°C	Square wave input		3.01	15.37	μA
					Resonator connection		3.20	15.56	μA
	I_{DD3} Note 6	STOP mode Note 8	T_A = −40°C				0.18	0.50	μA
			T_A = +25°C				0.23	0.50	μA
			T_A = +50°C				0.30	1.10	μA
			T_A = +70°C				0.46	1.90	μA
			T_A = +85°C				0.75	3.30	μA
			T_A = +105°C				2.94	15.30	μA

(**Notes** and **Remarks** are listed on the next page.)

3.4 AC Characteristics

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t_{TIH}, t_{TIL}				$1/f_{MCK}+10$			ns[Note]
TO00 to TO07, TO10 to TO17 output frequency	f_{TO}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV_{DD0} < 2.7 V				4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV_{DD0} < 2.7 V				4	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0	2.4 V ≤ V_{DD} ≤ 5.5 V		1			μs
		INTP1 to INTP11	2.4 V ≤ EV_{DD0} ≤ 5.5 V		1			μs
Key interrupt input low-level width	t_{KR}	KR0 to KR7	2.4 V ≤ EV_{DD0} ≤ 5.5 V		250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Note The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}
2.4V ≤ EV_{DD0} < 2.7 V : MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).
m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, $2.4\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution	$2.4\ V \le V_{DD} \le 5.5\ V$		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	$3.6\ V \le V_{DD} \le 5.5\ V$	2.125		39	μs
			$2.7\ V \le V_{DD} \le 5.5\ V$	3.1875		39	μs
			$2.4\ V \le V_{DD} \le 5.5\ V$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\ V \le V_{DD} \le 5.5\ V$	2.375		39	μs
			$2.7\ V \le V_{DD} \le 5.5\ V$	3.5625		39	μs
			$2.4\ V \le V_{DD} \le 5.5\ V$	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution	$2.4\ V \le V_{DD} \le 5.5\ V$			±0.60	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution	$2.4\ V \le V_{DD} \le 5.5\ V$			±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution	$2.4\ V \le V_{DD} \le 5.5\ V$			±4.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution	$2.4\ V \le V_{DD} \le 5.5\ V$			±2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output ($2.4\ V \le V_{DD} \le 5.5\ V$, HS (high-speed main) mode)		V_{BGR}[Note 3]			V
		Temperature sensor output voltage ($2.4\ V \le V_{DD} \le 5.5\ V$, HS (high-speed main) mode)		V_{TMPS25}[Note 3]			V

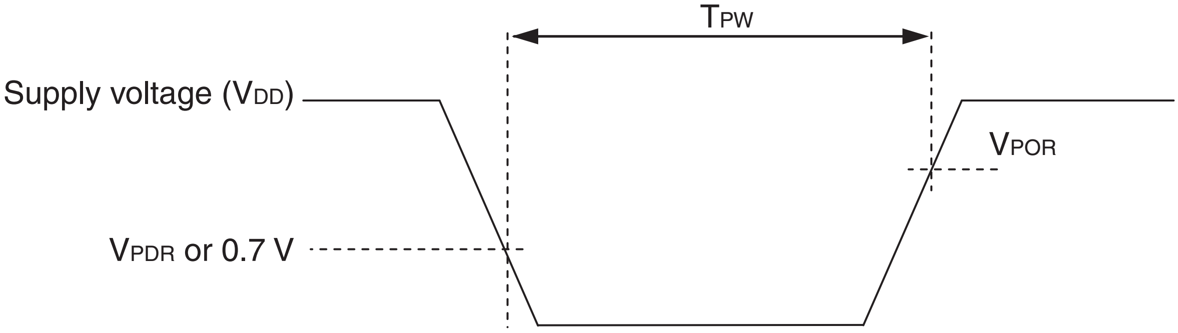
Notes
1. Excludes quantization error (±1/2 LSB).
2. This value is indicated as a ratio (%FSR) to the full-scale value.
3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

3.6.3 POR circuit characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

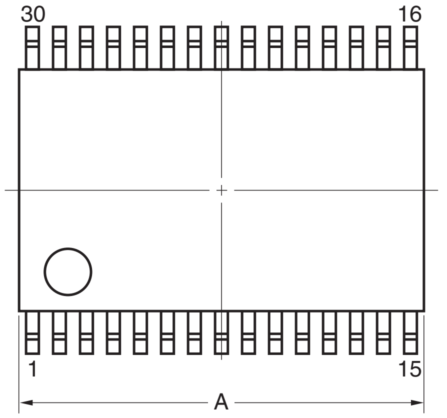
Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).

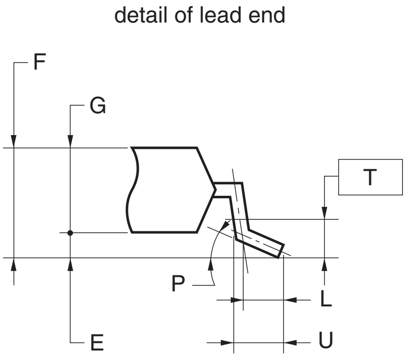


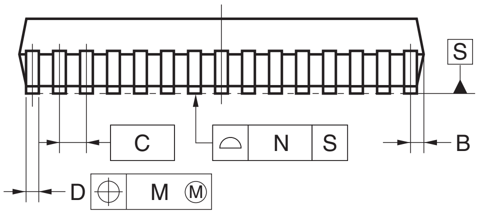
4.4 30-pin Products

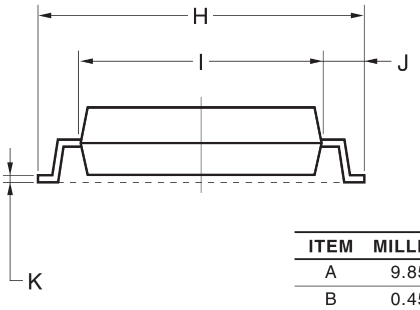
R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
R5F100AAGSP, R5F100ACGSP, R5F100ADGSP,R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18









ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
T	0.25
U	0.6±0.15

NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

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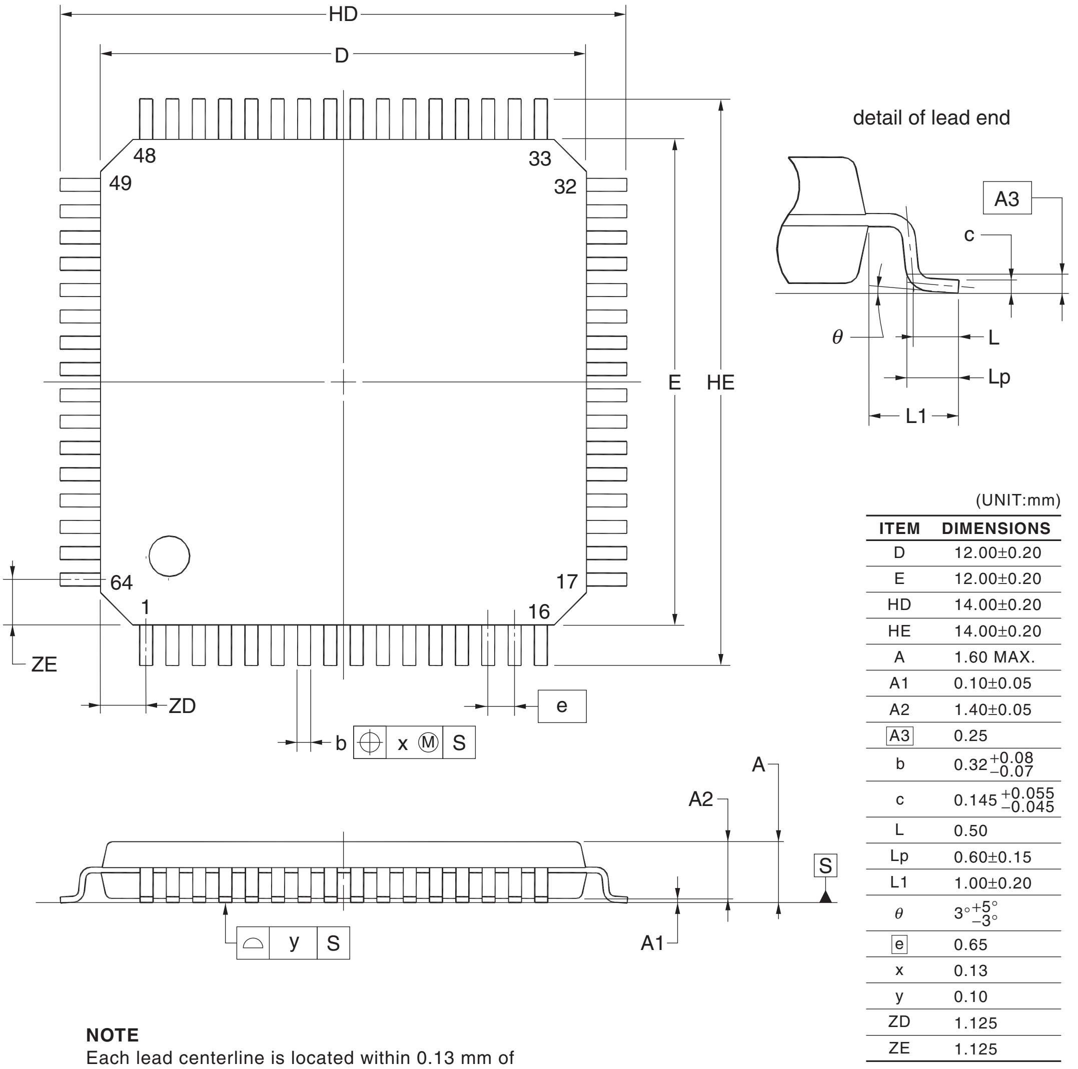
4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA
R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA
R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA
R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA
R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
$\boxed{\text{A3}}$	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
$\boxed{\text{e}}$	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

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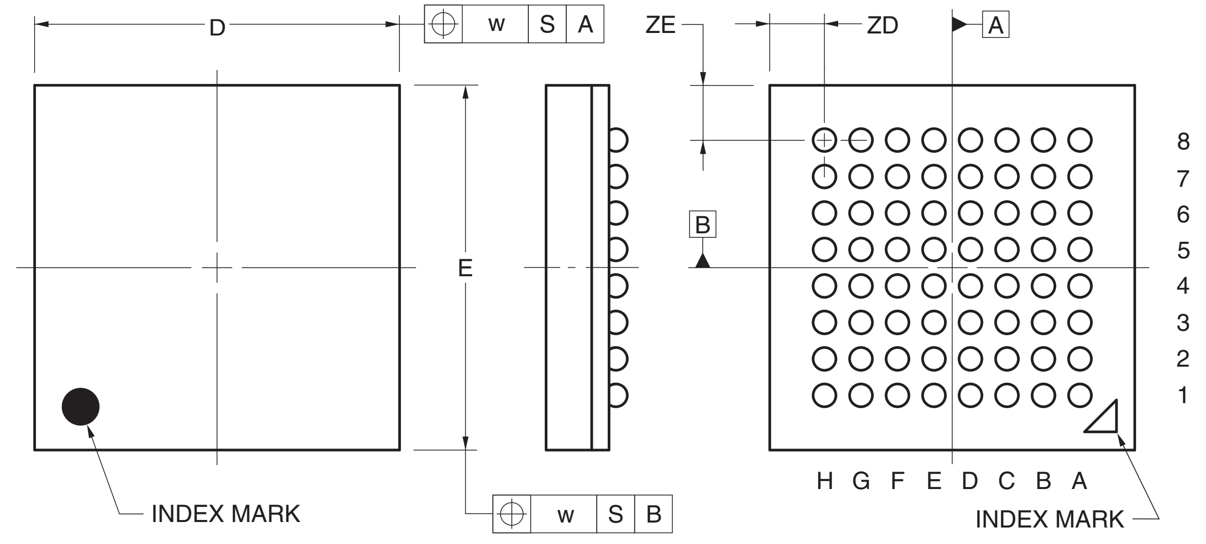
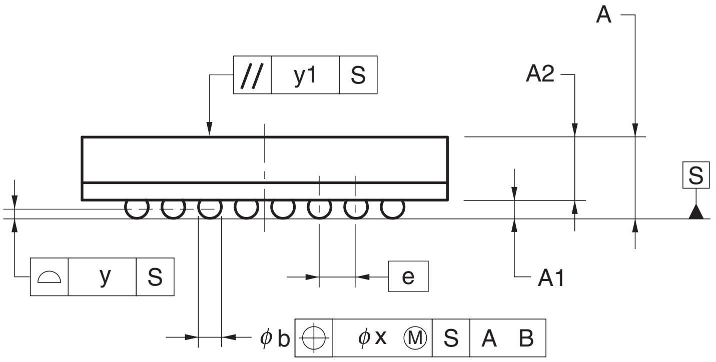
R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG,
R5F100LJABG
R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG,
R5F101LJABG
R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LHGBG,
R5F100LJGBG

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-VFBGA64-4x4-0.40	PVBG0064LA-A	P64F1-40-AA2-2	0.03





(UNIT:mm)

ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.15
A	0.89±0.10
A1	0.20±0.05
A2	0.69
e	0.40
b	0.25±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.60
ZE	0.60

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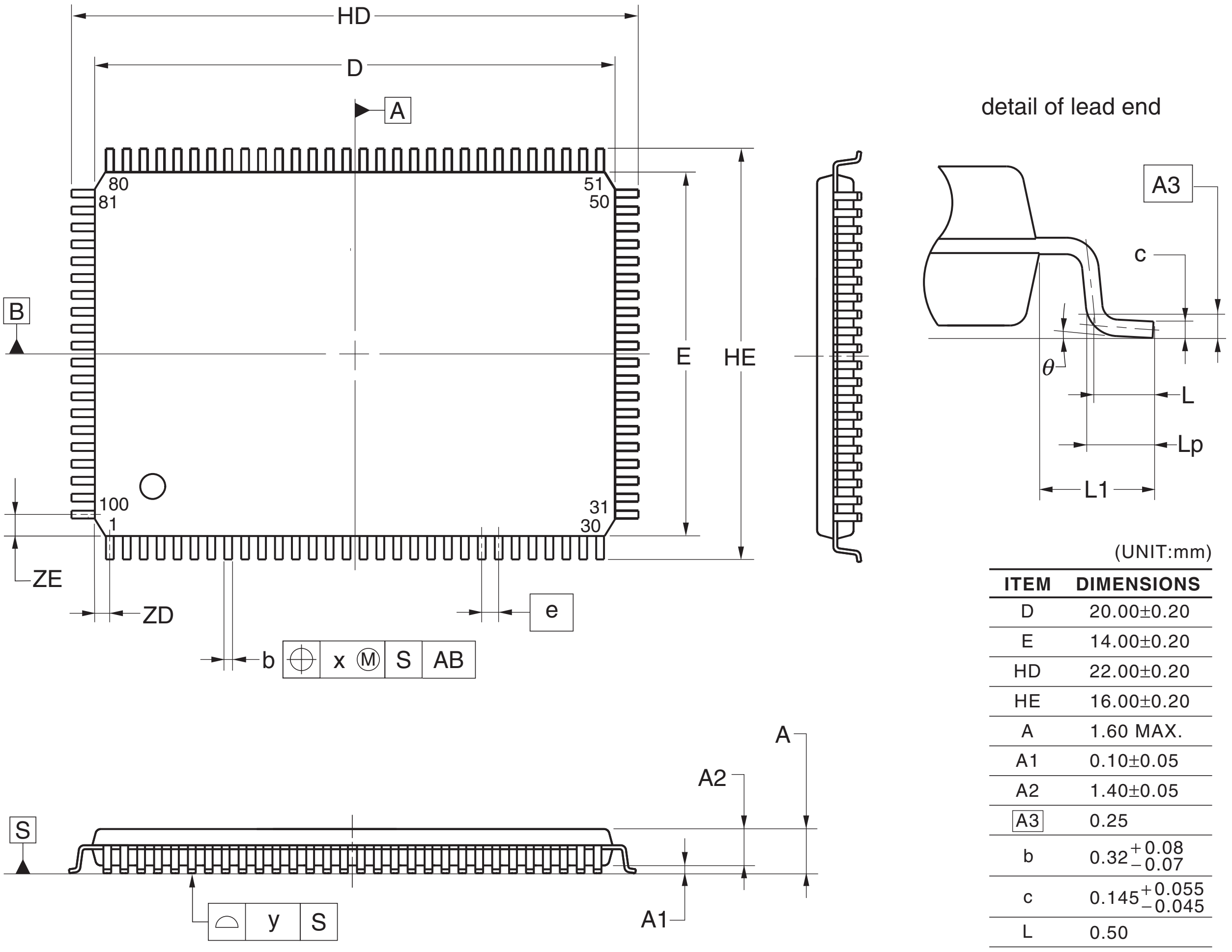
R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA
R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA
R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F100PLDFA
R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA
R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
$\boxed{A3}$	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
$\boxed{e}$	0.65
x	0.13
y	0.10
ZD	0.575
ZE	0.825

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